

4V Drive Pch+Pch MOSFET

SH8J62

Structure

Silicon P-channel MOSFET

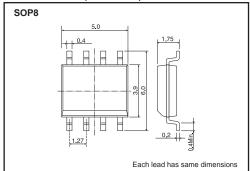
● Features

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

Application

Switching

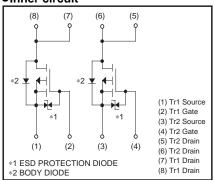
●Dimensions (Unit: mm)



Packaging specifications

	Package	Taping
Туре	Code	TB
	Basic ordering unit (pieces)	2500
SH8J62		0

●Inner circuit



● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

Parameter		Symbol		Limits	Unit	
Drain-source voltage		V _{DSS}		-30	V	
Gate-source voltage		Vgss		±20	V	
Drain current	Continuous	I_D		±4.5	А	
Drain current	Pulsed	I_{DP}	*1	±18	А	
Source current	Continuous	Is		-1.6	Α	
(Body diode)	Pulsed	Isp	*1	-18	А	
Total power dissipation		P _D	*2	2.0	W / TOTAL	
				1.4	W / ELEMENT	
Channel temperature		Tch		150	°C	
Range of Storage temperature		Tstg		-55 to +150	°C	

^{*1} Pw≤10μs, Duty cycle≤1%

^{*2} Mounted on a ceramic board

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●Electrical characteristics (Ta=25°C) <It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μА	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	-30	-	_	V	I _D = -1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	-1	μА	V _{DS} = -30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	_	-2.5	V	V _{DS} = -10V, I _D = -1mA
Static drain-source on-state resistance	R _{DS (on)} *	-	40	56	mΩ	I _D = -4.5A, V _G S= -10V
		-	55	77	mΩ	I _D = -2.5A, V _G S= -4.5V
		-	60	84	mΩ	I _D = -2.5A, V _G S= -4.0V
Forward transfer admittance	Y _{fs} *	3.5	_	_	S	V _{DS} = -10V, I _D = -4.5A
Input capacitance	Ciss	-	800	_	pF	V _{DS} = -10V
Output capacitance	Coss	-	120	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	110	-	pF	f=1MHz
Turn-on delay time	td (on) *	_	7	_	ns	I _D = -2.5A
Rise time	tr *	-	15	_	ns	V _{DD} ≒ −15V
Turn-off delay time	t _{d (off)} *	-	70	_	ns	V _G s= -10V R _L =6.0Ω
Fall time	t _f *	-	50	-	ns	R _G =10Ω
Total gate charge	Qg *	_	8.0	_	nC	V _{DD} ≒ –15V
Gate-source charge	Q _{gs} *	-	2.5	-	nC	I _D = -4.5A V _G s= -5V
Gate-drain charge	Q _{gd} *	-	3.0	_	nC	$R_L=3.3\Omega / R_G=10\Omega$

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp *	_	_	-1.2	V	I _S = -4.5A, V _G S=0V

^{*} Pulsed

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-10V

V_{GS}= -4.5V

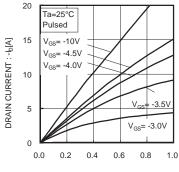
V_{GS}= -4.0V

Vcc= -3.8V

Ta=25°C

Pulsed

Electrical characteristic curves



DRAIN-SOURCE VOLTAGE: -VDS[V] Fig.1 Typical output characteristics(I)



DRAIN CURRENT: -l_b[A] 8 $V_{GS} = -3.2V$ 6 4 2 0 10

20

18

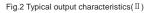
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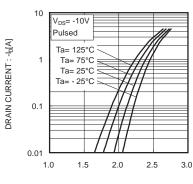
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10

DRAIN-SOURCE VOLTAGE: -VDS[V]





GATE-SOURCE VOLTAGE: -VGS[V]

Fig.3 Typical Transfer Characteristics

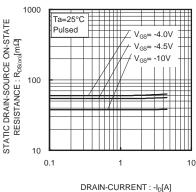
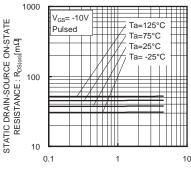
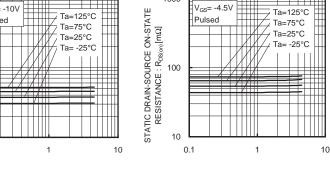


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current($\[I\]$)



DRAIN-CURRENT : -I_D[A] Fig.5 Static Drain-Source On-State

Resistance vs. Drain Current(${\rm I\hspace{-.1em}I}$)



DRAIN-CURRENT : -I_D[A]

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(${\mathbb II}$)

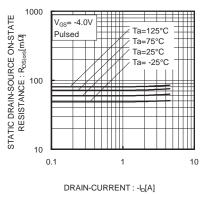


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

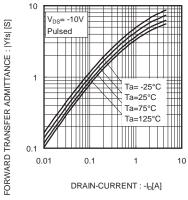


Fig.8 Forward Transfer Admittance vs. Drain Current

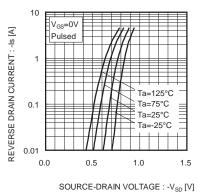
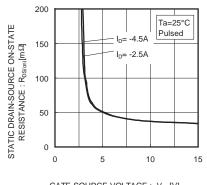
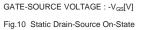


Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

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Resistance vs. Gate Source Voltage

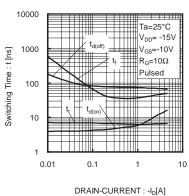
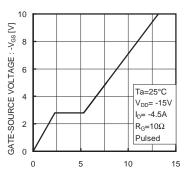
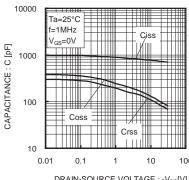


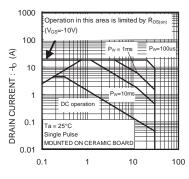
Fig.11 Switching Characteristics



TOTAL GATE CHARGE : Qg [nC]
Fig.12 Dynamic Input Characteristics



DRAIN-SOURCE VOLTAGE : -V_{ns}[V]
Fig.13 Typical Capacitance
vs. Drain-Source Voltage



DRAIN-SOURCE VOLTAGE : -V_{DS}[V] Fig.14 Maximum Safe Operating Area

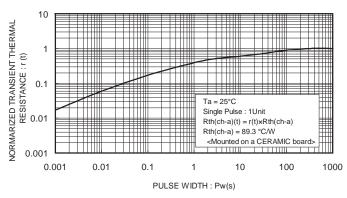


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

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●Measurement circuits

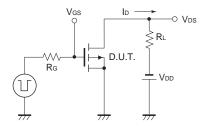


Fig.1-1 Switching Time Test Circuit

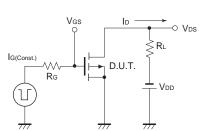


Fig.2-1 Gate Charge Test Circuit

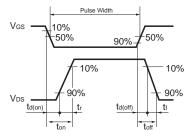


Fig.1-2 Switching Time Waveforms

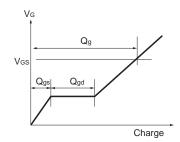


Fig.2-2 Gate Charge Waveform

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